Voltage-Tunable *Q* Factor in Photonic Crystal Microcavity

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A photonic crystal microcavity with the tunable Q factor has been implemented on the basis of a bound state in the continuum using the advanced liquid crystal cell technology platform. It has been shown that the Q factor of the microcavity changes from 100 to 360 in the voltage range of 0.6 V.

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Bound states in the continuum (BICs) are the nonradiative localized eigenmodes implemented in an open system. The 5 BIC was first reported by von Neumann and Wigner in 1929 as a solution of the problem for a quantum particle in the finite oscillating potential [1]. The wave function of a particle is localized, while its energy is positive and lies within a continuum of propagating states. The BIC is a general wave phenomenon, 10 which occures not only in quantum mechanics, but also in radio 11 physics, photonics, and acoustics [2–6]. Changing the param-12 eters of a system near the BIC, one can control the coupling 13 between a localized mode and the continuum of propagating 14 waves and thereby tune the radiation component of the sys-15 16 tem Q factor. In practice, due to the finite geometric length 17 of structures, imperfection of fabrication techniques used, and absorption of materials, the amplitude of the Fano resonances 18 with a finite *Q* factor [7–9] at the BIC points turns to zero. In 19 this case, we can speak about the implementation of quasi-BICs. 20 The BIC concept was used in various photonics applications, in 21 particular, in lasers [10, 11], sensors [12–15], waveguides [16, 17], 22 optical switches [18], nonlinear amplifiers [19], etc. According 23 to the mechanism of implementation, the BICs are divided in 24 several classes [2–6]. The symmetry-protected BICs (SP BICs) are 25 based on opposite symmetries of localized modes and propagat-26 ing waves, which yields the zero overlap integral [20, 21]. The 27 Friedrich-Wintgen (accidental) BICs (FW BICs) originate from 28 the destructive interference of waves outgoing from a cavity 29 [16, 22]. 30

According to the Lee's theorem [23], in a 1D multilayer model, 70

the transmission zeros and, consequently, BICs, cannot be implemented. This theorem, however, is not generalized to the 1D multilayers of anisotropic materials, in which, as in the 2D and 3D models, the BICs were also implemented [24–26]. The authors of [27, 28] demonstrated a trilayer waveguide consisting of birefringent materials, which supports the waveguide quasi-BICs. The rest 1D models that have been proposed to date are based on photonic crystals (PhCs) with an anisotropic defect layer [29–34].

In this study, an optical microcavity model [30] with the voltage-tunable *Q* factor is implemented on the basis of a BIC. Figure 1(a) shows a microcavity consisting of two identical mirrors formed from 1D PhCs separated by a liquid crystal (LC) resonator layer.

The PhCs were formed on glass substrates pre-coated with aluminum-doped zinc oxide (AZO) with a refractive index (RI) of $n_{AZO} = 1.8 + i0.062$ [35] (hereinafter, the RIs of all the materials are given for a wavelength of $\lambda = 570$ nm) and a thickness of $d_{AZO} = 100$ nm. The PhC includes N = 8 periods consisting of a silicon nitride (Si₃N₄) layer and a silicon dioxide (SiO₂) layer formed by plasma-enhanced chemical vapor deposition. The RIs and layer thicknesses are $n_{\text{Si}_3\text{N}_4} = 2.15$ [36], $d_{\rm Si_3N_4} = 80$ nm and $n_{\rm SiO_2} = 1.45$ [37], $d_{\rm SiO_2} = 153$ nm. To obtain the symmetry, the PhC was additionally coated with an unpaired Si₃N₄ layer. Polyvinyl alcohol (PVA) layers with an RI of $n_{PVA} = 1.48$ [38] and a thickness of $d_{PVA} = 100$ nm were formed on each PhC by the spin-coating method. The mechanical rubbing of the PVA layers ensured a homogeneous planar alignment of the LC. The PhC mirrors were placed into a metal holder with tuning screws to make a uniform gap, which was determined by teflon spacers with a thickness of about d = 9.57µm. The gap between PhC mirrors was filled by 4-pentyl-4'cyanobiphenyl (5CB) nematic LC with RIs of $n_{\perp} = \sqrt{\varepsilon_{\perp}} = 1.55$ and $n_{\parallel} = \sqrt{\varepsilon_{\parallel}} = 1.74$ [39–41] by a capillary method. The preferred alignment of the long axes of LC molecules is described by the unit vector $\mathbf{a} = [\cos(\phi)\cos(\theta), \sin(\phi)\cos(\theta), \sin(\theta)],$ which is called the director [42]. In nematic LC the director coincides with the orientation of optical axis (OA) determined, according to Fig. 1(a), as a direction of the major semiaxis of the



Fig. 1. (a) PhC microcavity model. The inset shows the orientation of an LC permittivity ellipsoid. The microcavity is presented in the photograph. (b) Polarizing optical microscope images of the LC layer texture taken in crossed polarizers at different applied voltages. R1 and R2 are the PVA rubbing directions. Crossed double arrows show the direction of the polarizer (P) and analyzer (A). (c) Scheme for measuring the microcavity transmittance spectra. The TE and TM vectors show the direction of the electric field at the corresponding polarizations. The photograph in the inset shows the microcavity with hemispherical lenses. (d) Measured (dashed line) and calculated (solid line) PhC transmittance spectra for the TE (red) and TM (blue) waves. The top and bottom plots correspond to the normal incidence of light and the incidence at the Brewster's angle, respectively. The photograph of the PhC is shown in the inset.

71 permittivity ellipsoid.

104 Figure 1(b) presents polarizing microscopy images of the 72 105 optical texture of the LC layer. When the rubbing direction 73 is parallel to the polarizer or analyzer, a uniform dark texture ¹⁰⁶ 74 can be seen. The maximum intensity of the transmitted light 107 75 is observed upon rotation of the crossed polarizers by 45° (the $_{108}$ 76 top row in Fig. 1(b)). These optical textures confirm the planar $_{109}$ 77 LC alignment. The conducting transparent AZO layers make 110 78 it possible to apply 1 kHz AC voltage to the LC layer to avoid 111 79 blocking of the external field by ions in the LC. It can be seen in 112 80 Fig. 1(b) (the middle and bottom rows) that the applied voltage 113 81 changes the color of the optical texture of the LC layer, which is 114 82 evidence of the change in the LC orientational structure. 115 83

Figure 1(c) presents a scheme for measuring the microcav- ¹¹⁶ 84 ity transmittance spectra. The incoherent radiation of a halo- 117 85 gen lamp from a Thorlabs OSL2 source propagates through 118 86 an optical fiber and focuses with a collimator in a spot about 119 87 2 mm in diameter. After the transmittance through a polar- 120 88 izer, the TE-polarized (TE wave) or TM-polarized (TM wave) 121 89 radiation passes into the microcavity through hemispherical 122 90 glass lenses with an RI of $n_G = 1.5$. The lenses are glued 123 91 to the glass substrates of the microcavity using immersion 124 92 oil with an RI of $n_{Oil} = 1.5$ to eliminate an air gap. In- 125 93 troducing the radiation through the glass lenses at an angle 126 94 of $\theta_{in} = \arcsin \left[(n_{Si_3N_4}/n_G) \sin \left(\arctan \left(n_{SiO_2}/n_{Si_3N_4} \right) \right) \right] \approx 53^{\circ}$, ¹²⁷ 95 one can implement the Brewster effect for the TM wave at 128 96 the Si₃N₄/SiO₂ interfaces [43]. The outgoing radiation is col-97



Fig. 2. Transmittance spectra of the optical microcavity at different azimuthal angles ϕ of the LC OA for (a) TE and (b, c) TM waves. The left-hand panels show the measured spectra and the right-hand panels present the calculated ones. The black rectangle in (b) is zoomed in (c). Solid lines in (c) correspond to the solutions of the problem on the eigenvalues of an open cavity for the even (magenta lines) and odd (cyan lines) modes. The solutions are shown by circles for the SP BIC problem and by crosses for FW BIC problem.

lected in a fiber optic collimator connected to an OCEAN FX-UV-VIS spectrometer. The microcavity is mounted on an Thorlabs KPRM1E/M motorized precision rotation stage, which makes it possible to change the azimuthal angle ϕ of the LC OA orientation. The external voltage applied to LC layer using an Aktakom AWG-4150 function generator can change the polar angle θ of the LC OA orientation. The value and frequency of the applied voltage are controlled with an Aktakom ABM-4552 multimeter. The operation of all the units and recording of the spectra are monitored using a personal computer.

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Figure 1(d) presents the PhC transmittance spectra measured and calculated by the Berreman transfer matrix method [44]. It can be seen that, under normal incidence of light, there is a photonic band gap (PBG) with the center at $\lambda_{PBG} = 800$ nm for both the TE and TM waves. When the light falls at the Brewster's angle, the PBG shifts to the visible range and $\lambda_{PBG} = 570$ nm for the TE wave. The PBG for the TM wave vanishes due to the Brewster effect. Thus, in a certain wavelength range, the PhC is nontransparent for the TE waves and transparent for the TM ones.

Figure 2 illustrates the transformation of the transmittance spectra of the microcavity filled with the LC upon variation in the azimuthal angle ϕ of the LC OA orientation. Figure 2(a) shows that the spectrum does not change in the PBG region for the TE waves, which demonstrates the absence of resonances. On the other hand, the spectrum for the TM waves contains numerous resonant lines in the same spectral range (see Fig. 2(b)). The rotation of the LC OA causes the change in the position and width of the resonant lines. It is consequence of the changes both in the optical width of the LC layer and in the coupling between the localized modes and the waves propagating in the PhC waveguides.

The behavior of the spectra can be qualitatively explained 130 by dividing the total electric field strength *E* of light in the LC 131 into contributions of the ordinary wave (o wave) Eo and ex-132 traordinary wave (e wave) E_e : $E = E_e + E_o$. The polariza-133 tion directions of the o and e waves are given by the vectors 134 $E_{\rm o} = E_{\rm o} \left[a \times \kappa_{\rm o} \right]$ and $E_{\rm e} = E_{\rm e} \left| a - \frac{\varepsilon_{\rm e}(\alpha)}{\varepsilon_{\rm o}} \kappa_{\rm e}(\kappa_{\rm e}a) \right|$ [45], respec-135 tively. Here, $\kappa_{o,e} = [\kappa_{o,ex}; 0; \kappa_{o,ez}]$ is the unit vector along the 136 direction of propagation of the o, e wave; $\varepsilon_0 = \varepsilon_{\perp}$ is the per-137 mittivity for the o wave, and $\varepsilon_e(\alpha)$ is the permittivity for the e 138 wave, which has the values $\varepsilon_{\perp} \leq \varepsilon_{e}(\alpha) \leq \varepsilon_{\parallel}$ and is determined 139 by the angle α between the vectors *a* and κ_{e} . Since the o and e 140 141 waves have different permittivities, they have different phase incursions during propagation through the LC layer. In the gen-142 eral case, for the angles $\phi \neq 0$ and $\theta \neq 0$, all the components of 143 the o and e waves are nonzero: $E_{o, e} = [E_{o, ex}, E_{o, ey}, E_{o, ez}]$; i.e., 144 the TE and TM waves are mixed in the LC layer. 145

The measured and calculated spectra in Fig. 2(b) show that 146 the resonant lines collapse at $\phi = 0$ and $\phi = \pi/2$. The positions 147 of the collapses coincide with the solutions of the problem on 148 the SP BICs [30], which are shown by circles in Fig. 2(c). At 149 $\theta = 0$ and $\phi = 0$, the o wave has a projection only on the TE 150 wave: $E_0 = [0, E_{ov}, 0]$ and the e wave has a projection only on 151 the TM wave: $E_e = [E_{ex}, 0, E_{ez}]$ (see Figs. 1(a,b)). At $\theta = 0$ and 152 $\phi = \pi/2$, the situation is opposite: $E_0 = [E_{ox}, 0, E_{oz}], E_e =$ 153 $[0, E_{ev}, 0]$. This means that, in these cases, the propagating TM 154 wave is not converted into the TE wave, which can be localized 155 due to the PBG. This explains qualitatively also the red shift of 156 the resonant lines in Fig. 2(b) with increasing angle ϕ . For the 157 localized TE waves with the only *y* component, the RI changes 158 from the minimum value $n|_{\phi=0}^{\theta=0} = n_{\perp}$ to the maximum one 159 $n|_{\phi=\pi/2}^{ heta=0}=n_{\parallel}.$ The behavior of the resonant lines is confirmed 160 also by the numerical calculation and solution of the problem 161 on the eigenvalues of an open system [30]. Figure 2(c) shows the 162 spectral position of the resonances $\lambda_0 = 2\pi/\omega_0$ obtained from 163 the eigenvalue $\omega_r = \omega_0 - i\gamma$. 164

The collapses of the resonant lines can be observed also at the 165 intermediate angles $\phi \neq 0, \pi/2$. The positions of the collapses 166 coincide with the solutions of the problem on the FW BICs [30] 167 shown by crosses in Fig. 2(c). When the total projection of the 192 168 contributions of the o and e waves on the TM wave at the output 169 193 of LC layer is zero $E_x = E_{ex} + E_{ox} = 0$, the energy cannot be 170 194 brought out of the cavity by the propagating TM waves. This 17 differs the SP BICs from the FW BICs, in which not only the 196 172 TE component of the total field is localized in the LC layer due 197 173 to the PBG, but also the TM component, due to the destructive 198 174 interference of the waves at the output of the LC layer [30]. As 199 175 it was shown in [30, 34], the LC layer in this case plays the role 200 176 of a full-wave phase plate, which recovers the state of polar-177 201 ization at the output identical to that at the input [46]. In both 202 178 179 cases, when the SP BICs or FW BICs are implemented, there 203 is no coupling between the localized and propagating waves, 204 180 which makes zero radiation component of the imaginary part 205 181 of the eigenvalue $\gamma_{\rm rad}=$ 0; $\gamma=\gamma_{\rm rad}+\gamma_{\rm ext}.$ In the spectrum it $_{_{206}}$ 182 appears as a vanishing amplitude of the resonant line, the width 207 183 of which at the quasi-BIC point is only determined by the nonra- 208 184 diative extinction loss, including the absorption and scattering 185 209 $\Delta \omega = 2\gamma_{\text{ext}}$. Between the two angles ϕ corresponding to the BIC 186 implementation, the radiation component of the resonant line 211 18 width $\gamma_{\rm rad}$ changes from zero to the finite value and vice versa. ²¹² 188 It allows to consider this situation as the implementation of the 213 189 resonances with the tunable quality factor $Q = \omega_0/2\gamma$. 190 214

Figure 3 illustrates the transformation of the transmittance 215 19



Fig. 3. (a–e) Measured transmittance spectra of the optical microcavity at different values of applied voltages U; $U_{th} \approx 1.2 \text{ V}$ is the threshold voltage for LC reorientation. (f) Q factor of the resonant line (red dots in (e)) calculated from the FWHM.

spectra of the microcavity upon variation in the voltage applied to the LC layer at constant azimuthal angles ϕ of the LC OA orientation. It can be seen from the spectra that, at the voltages below the threshold value of the Fredericks effect [42] $U < U_{th}$ the positions and widths of the resonant lines do not change. The voltage $U = U_{th}$ corresponds to the beginning of the LC reorientation. With a further increase in the voltage $U \ge U_{th}$ the director rotates toward the external electric field direction (along the *z* axis); i.e., the polar angle θ increases (see Fig. 1(a)). At $\phi = 0$, for any polar angle θ , the o wave has a projection only on the TE wave, while the e wave has a projection only on the TM wave. The propagating TM wave is not converted to the TE wave at any applied voltage U. Therefore, the weak resonances in Fig. 3(a), which have fixed widths, correspond to the localized TM waves. They arise due to the low reflectance at the interface between the PVA layer and the first Si₃N₄ layer. These resonances, as a background of the resonances with the tunable Q factor, can also be seen in Fig. 3(b) up to the threshold voltage, as well as in Figs. 2(b,c) at $\phi = 0, \pi/2$. Intermixing of the TE and TM waves in the LC layer in the general case of $\phi \neq 0$ and $\theta \neq 0$ leads to the occurrence of the resonances with the tunable Q factor, as can be seen in Figs. 3(b–e). At certain voltages U, one can see the collapses of the resonant lines corresponding to the FW BICs (the mechanism of their

implementation was explained above). At an external voltage 279 216 of $U > 5U_{th}$, the resonant lines in the spectrum remain almost 217 280 invariable. This is due to the fact that, at high voltages, the ²⁸¹ 218 282 LC director, except for the thin surface layer, aligns along the 219 283 applied field direction [42]. This explains also the blue shift 220 of the resonant lines, since, in the limit case of high voltages, 221 285 the angle is $\theta = \pi/2$ and for the localized TE wave, which has 222 286 only the *y* component the LC RI is equal to the minimum value 223 287 $n|_{\phi}^{\theta=\pi/2} = n_{\perp}$ (Fig. 1(a)). In Fig. 3(f), the *Q* factor is presented 224 288 for one of the resonant lines from Fig. 3(e). It can be seen that 289 225 290 the *Q* factor sharply increases upon approaching the FW BIC 226 291 in the vicinity of U \approx 4.1U_{th}. The measured *Q* factor changes 227 292 from 100 to 360 in the voltage range from $3.4U_{th}$ to $3.9U_{th}$, i.e., 228 293 by $0.5U_{th} = 0.6$ V. The sensitivity of the *Q* factor to the change 229 201 in the applied voltage is $\Delta Q / \Delta U = 433 \text{ V}^{-1}$. 230 295

Thus, a photonic crystal microcavity with a liquid crystal 231 296 defect layer was created, where on the basis of the concept of 297 232 the bound state in the continuum, we first demonstrated the 298 233 efficient voltage control by both the position [47–51] and width 299 234 of the resonant lines. The proposed model can be used for design 300 235 of energy-efficient photonic devices with the voltage-tunable Q 301 236 302 factor. 237

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242Data Availability Statement. The data that support the findings309243of this study are available from the corresponding author, P.S.P., upon310244reasonable request.311

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